

ABSTRACT

An opening is formed in a light-absorbing layer on a mask by applying a second resist above a first resist on the layer . A first exposure step with subsequent development of the second resist leads to the formation of a first opening in the developed second resist. The first resist is uncovered on an area within the opening. A second exposure step is performed by irradiation of the mask in a second segment, which is laterally offset with respect to the first opening, so that an incomplete portion of the area of the uncovered first resist is exposed within the opening. After a further development step and an etching step with formation of a second opening in the developed first resist with a transfer of the portion into the light-absorbing layer, this opening has a diameter smaller than both the first and the second segment.